## WHAT IS CLAIMED IS:

1. A photosensitive polymer having a trifluorovinyl derivative monomer as a repeating unit and having a weight average molecular weight of about 3,000 to about 100,000, the trifluorovinyl derivative represented by the following formula:

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wherein X is a  $C_1$ - $C_5$  alkyl group with or without fluorine substituent, and G is at least one selected from the group consisting of:

$$F_{3}C \xrightarrow{\bigcap} F_{3}C \xrightarrow{\bigcap} O \xrightarrow{\bigcap} O$$

$$F_{3}C \xrightarrow{\bigcap} O \xrightarrow{\bigcap} CF_{3}$$

$$O \xrightarrow{\bigcap} O \xrightarrow{\bigcap} O$$

- wherein R is a primary, secondary or tertiary  $C_1$ - $C_{10}$  alkyl, tetrahydropyranyl, tetrahydrofuranyl or 1-ethoxyethyl group, and n is an integer from 1 to 5.
- 2. The photosensitive polymer according to claim 1, wherein the photosensitive polymer is a polymerization product of the trifluorovinyl derivative monomer and at least one monomer selected from the group consisting of a fluorine-substituted or unsubstituted (meth)acrylic acid monomer, (meth)acrylate monomer, styrene monomer, norbornene monomer, tetrafluoroethylene monomer and maleic anhydride monomer.

## 3. A resist composition comprising:

a photosensitive polymer having a trifluorovinyl derivative monomer as a repeating unit and having a weight average molecular weight of about 3,000 to about 100,000, the trifluorovinyl derivative represented by the following formula:

wherein X is a  $C_1$ - $C_5$  alkyl group with or without fluorine substituent, and G is at least one selected from the group consisting of:

$$F_{3}C \xrightarrow{()}_{RO} n \qquad F_{3}C \xrightarrow{()}_{CF_{3}} n \qquad F_{3}C \xrightarrow{()}_{CF_{3}} 0$$

wherein R is a primary, secondary or tertiary  $C_1$ - $C_{10}$  alkyl, tetrahydropyranyl, tetrahydrofuranyl or 1-ethoxyethyl group, and n is an integer from 1-5; and

a photoacid generator in an amount of about 1 to about 15% by weight based on the total weight of the photosensitive polymer.

4. The resist composition according to claim 3, wherein the photosensitive polymer is a polymerization product of the trifluorovinyl derivative monomer and at least one monomer selected from the group consisting of a fluorine-substituted or unsubstituted (meth)acrylic acid monomer, (meth)acrylate monomer, styrene monomer, norbornene monomer, tetrafluoroethylene monomer and maleic anhydride monomer.

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- 5. The resist composition according to claim 3, further comprising an organic base in an amount of about 0.01 to about 2.0% by weight based on the total weight of the photosensitive polymer.
  - 6. A patterning method comprising:
- (a) coating a resist composition on a substrate, wherein the resist composition comprises:

a photosensitive polymer having a trifluorovinyl derivative monomer as a repeating unit and having a weight average molecular weight of about 3,000 to about 100,000, the trifluorovinyl derivative represented by the following formula:

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wherein X is a  $C_1$ - $C_5$  alkyl group with or without fluorine substituent, and G is at least one selected from the group consisting of:

$$F_{3}C \xrightarrow{()}_{RO} n \qquad F_{3}C \xrightarrow{()}_{CF_{3}} n \qquad F_{3}C \xrightarrow{()}_{CF_{3}} 0$$

wherein R is a primary, secondary or tertiary  $C_1$ - $C_{10}$  alkyl, tetrahydropyranyl, tetrahydrofuranyl or 1-ethoxyethyl group, and n is an integer from 1-5; and

a photoacid generator in an amount of about 1 to about 15% by weight based on the total weight of the photosensitive polymer;

- (b) exposing the resist layer using an exposure light source having a wavelength of 157 nm or less; and
  - (c) developing the exposed resist layer to form a resist pattern.

7. The patterning method of claim 6, wherein the photosensitive polymer is a polymerization product of the trifluorovinyl derivative monomer and at least one monomer selected from the group consisting of a fluorine-substituted or unsubstituted (meth)acrylic acid monomer, (meth)acrylate monomer, styrene monomer, norbornene monomer, tetrafluoroethylene monomer and maleic anhydride monomer.

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8. The patterning method of claim 6, wherein the resist composition further comprises an organic base in an amount of about 0.01 to about 2.0% by weight based on the total weight of the photosensitive polymer.